

Title (en)
METHOD FOR PRODUCING AN OPTOELECTRONIC SEMICONDUCTOR COMPONENT AND OPTOELECTRONIC SEMICONDUCTOR COMPONENT

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES OPTOELEKTRONISCHEN HALBLEITERBAUELEMENTS UND OPTOELEKTRONISCHES HALBLEITERBAUELEMENT

Title (fr)
PROCÉDÉ DE FABRICATION D UN COMPOSANT OPTOÉLECTRONIQUE À SEMI-CONDUCTEURS ET COMPOSANT OPTOÉLECTRONIQUE À SEMI-CONDUCTEURS

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Abstract (en)
[origin: WO2010040331A1] The invention relates to a method for producing an optoelectronic semiconductor component, wherein an epitaxial layer sequence (5), a contact layer (6), and a barrier layer (7) are applied by epitaxial growth onto an epitaxial growth substrate (1), and the epitaxial layer sequence (5) is structured to form individual semiconductor bodies (8) by generating furrows (9) in the epitaxial layer sequence (5). Subsequently, a dielectric layer (11) and preferably a mirror layer (21) are applied at least to the lateral edges (10) of the semiconductor bodies (8) exposed in the furrows (9). Thereafter, the semiconductor bodies (8) are connected to a carrier body (14) using a solder layer (13) on a side facing away from the epitaxial growth substrate (1), wherein the furrows (9) between the semiconductor bodies (8) are filled by the solder layer (13), and the epitaxial growth substrate (1) is then removed.

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